



# PRODUCT/PROCESS CHANGE NOTIFICATION

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PCN HED-AUD/08/3768  
Notification Date 06/05/2008

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**PENTAWATT/HEPTAWATT ASSEMBLY & TESTING TRANSFER FROM  
TOA-PAYOH TO BOUSKOURA**

**AUD - AUDIO**

**Table 1. Change Implementation Schedule**

Forecasted implementation date for change	06-Aug-2008
Forecasted availability date of samples for customer	25-Jun-2008
Forecasted date for <b>STMicroelectronics</b> change Qualification Plan results availability	29-May-2008
Estimated date of changed product first shipment	04-Sep-2008

**Table 2. Change Identification**

Product Identification (Product Family/Commercial Product)	ALL PRODUCTS IN PENTAWATT & HEPTAWATT PACKAGE
Type of change	Package assembly location change
Reason for change	ASSY LINE CLOSURE IN TOA-PAYOH
Description of the change	Pentawatt & Heptawatt production transfer from Toa-Payoh plant (Singapore) to Bouskoura 2000 plant (Morocco). Production in Bouskoura will be leadfree.
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	"CZ" AS PRODUCTION AREA FOR BOUSKOURA
Manufacturing Location(s)	



## DOCUMENT APPROVAL

Name	Function
Angelici, Marco	Division Marketing Manager
Onetti, Andrea Mario	Division Product Manager
Piccoli, Massimo	Division Q.A. Manager



## **PENTAWATT / HEPTAWATT ASSEMBLY & TESTING TRANSFER FROM TOA-PAYOH TO BOUSKOURA**

### **WHAT:**

Following Company package roadmap to concentrate in Bouskoura 2000 plant the small watt assembly activity, we are on going to transfer there the assembly & testing of the Pentawatt & Heptawatt products (all splittings: vertical, horizontal and in line)

In 2004, STM already completed a first transfer of Pentawatt/Heptawatt products to Bouskoura (PCN HPC-AUD/06/1627 & HED-AUD/07/2239 ) and the plant is fully operative since middle of 2004. The products involved in this second transfer are the last ones remaining in Toa-Payoh for the Audio Division.

Due to the changes introduced on Pentawatt/Heptawatt after 2004, production in Bouskoura for all the involved products will be 2 mils copper wires and leadfree pure tin post plating (RoHS compliant – e3 marking on the parts).

In addition, we will change the frames from the actual bicomponent frames (slug & frame welded together before assy) to monocomponent frame (one piece frame) as per attached pictures. This frame is already qualified in Bouskoura.

### **WHY:**

Company package roadmap

### **HOW:**

Reliability evaluation report ER002107AG6053 covers all the type of products involved in this PCN.

### **WHEN:**

We will start to deliver from Bouskoura from beginning of September 2008.

# **SMALL-WATT PACKAGES WITH “MONOCOMPONENT” LEADFRAME RELIABILITY EVALUATION REPORT**

## ***Abstract***

HEPTAWATT and PENTAWATT packages assembled in BOUSKOURA with the new MONOCOMPONENT lead-frame have been successfully evaluated on two APG test-vehicles.

Main aim of the reliability exercise was to complete the set of results collected by HPC Group, with the addition of temperature cycling performed in conformity with AEC-Q100 “grade 1” requirements.

## ***Conclusion***

On the basis of the results summarized in the present report, HEPTAWATT and PENTAWATT packages assembled in BOUSKOURA with the new MONOCOMPONENT lead-frame can be qualified as far as reliability is concerned.

## ATTACHMENT 1: RELIABILITY TESTS DESCRIPTION

TEST NAME	DESCRIPTION	PURPOSE
<b>TCT:</b> Temperature Cycles Test	The device is submitted to cycled temperature excursions, between a hot and a cold chamber in air atmosphere.	To investigate failure modes related to the thermo-mechanical stress induced by the different thermal expansion of the materials interacting in the die-package system. Typical failure modes are linked to metal displacement, dielectric cracking, moulding compound delamination, wire-bonds failure, die-attach layer degradation.
<b>HTS:</b> High Temperature Storage	The device is stored in unbiased condition at the max. temperature allowed by the package materials, sometimes higher than the max. operative temperature.	To investigate the failure mechanisms activated by high temperature, typically wire-bonds solder joint ageing, data retention faults, metal stress-voiding.

## ATTACHMENT 2: RESULTS FROM HPC QUALIFICATION

TEST NAME	CONDITIONS [SPEC]	STV8172A REJ./SS	STV9302A REJ./SS	NOTES
TCT	Ta=-40/+150°C, 1000 cycles	0/50	0/(50x2)	-
PPT	P=2atm, Ta=121°, 240h	0/50	0/(50x2)	-
HTS	Ta=175°C, 500h	0/50	0/(50x2)	1
HTRB	Ta=85°C, Tj=150°C, 1000h	-	0/(20x2)	2

**NOTES:**

- <sup>1</sup> HTS test has been continued up to 1000h in order to investigate the wear-out curve. One parametric failure has been found on the 2<sup>nd</sup> lot of STV9302A. Being the failure root-cause identified in the molding-compound stress and taking into account that the concerned material does not have stable and controlled mechanical properties above 150°C (max. operative temperature), the failure mechanism is not realistic in the field application environment.
- <sup>2</sup> High Temperature Reverse Bias test, devices biased in static configuration at their maximum allowed supply voltage.

**Construction note**

<b>Technical code :</b>	STV8172A	STV9302A
<b>Diffusion process :</b>	B50II	B50II
<b>Wafer diameter :</b>	6"	6"
<b>Diffusion site :</b>	Ang Mo-Kio	Ang Mo-Kio
<b>Die size (mm<sup>2</sup>) :</b>	2.71 x 1.88	2.10x2.30
<b>Passivation :</b>	SiN	SiN
<b>Back finishing :</b>	Cr/Ni/Au	Cr/Ni/Au
<b>Package name :</b>	HEPTAWATT	HEPTAWATT
<b>Assembly site :</b>	BOUSKOURA	BOUSKOURA
<b>Leadframe :</b>	HW 7L Mon bare copper	HW 7L Mon bare copper
<b>Die attach :</b>	Pb/Ag/Sn	Pb/Ag/Sn
<b>Wire bonding :</b>	Cu, 2 mil	Cu, 2 mil
<b>Molding compound :</b>	SUMITOMO 6300HR	SUMITOMO 6300HR
<b>Lead finishing :</b>	Matte tin	Matte tin



**Reliability test conditions and results**

TEST NAME	CONDITIONS [SPEC]	REJ./S.S.	NOTES
TCT	Ta=-65/+150°C, 1000 cycles	L570 lot 1 0/50 L570 lot 2 0/50 L540 lot 3 0/50	1, 2, 3
HTS	Ta=150°C, 1000h	L570 lot 1 0/45 L570 lot 2 0/45 L540 lot 3 0/45	2

**NOTES:**

- <sup>1</sup> SAM analysis did not show any remarkable delamination at the die-molding compound interface, on the lead tips and through the die-attach layer. Detail in attachment n.3.
- <sup>2</sup> Wire bonding strength after the stress has been successfully verified through wire-pull test, performed in accordance with AEC-Q100 requirement. A few bonds failed in ball-lift mode, but the relevant residual pull loads are still high, especially taking into account the impact of the molding compound decap etch which is not selective to copper. Detail in attachment n.3.
- <sup>3</sup> Visual and SEM inspections after the stress test have pointed out no remarkable degradation of silicon passivation, metal interconnects, stitch bonds on internal lead-tips. Detail in attachment n.3.

**Construction note**

	TV1	TV2
<b>Technical code :</b>	K87X*L570TOX	K87E*L540DAX
<b>Diffusion process :</b>	BIP	BIP
<b>Wafer diameter :</b>	5"	5"
<b>Diffusion site :</b>	Ang Mo-Kio	Ang Mo-Kio
<b>Die size (mm<sup>2</sup>) :</b>	1.39 x 1.43	1.86 x 2.30
<b>Metal levels :</b>	1,Al	1,Al
<b>Passivation :</b>	SiN	SiN
<b>Back finishing :</b>	Cr/Ni/Au	Cr/Ni/Au
<b>Package name :</b>	HEPTAWATT	PENTAWATT
<b>Assembly site :</b>	BOUSKOURA	BOUSKOURA
<b>Leadframe :</b>	HW 7L Mon bare copper	PW 5L Mon bare copper
<b>Die attach :</b>	Pb/Ag/Sn	Pb/Ag/Sn
<b>Wire bonding :</b>	Cu,2 mil	Cu,2 mil
<b>Molding compound :</b>	SUMITOMO 6300HR	SUMITOMO 6300HR
<b>Lead finishing :</b>		
<b>Lot_id :</b>	CZ6160630 (sub-lots 1 and 2)	CZ61605PZY

**Attachments**

- 1) Reliability tests description
- 2) Results from HPC Group qualification
- 3) Physical analysis report

## ATTACHMENT 3: PHYSICAL ANALYSIS REPORT

**Technical code** : K87X\*L570TOX  
K87E\*L540DAX

**Package** : HEPTAWATT (HW)  
PENTAWATT (PW)

**Lot(s)\_id** : Lot 1 CZ6160630  
Lot 2 CZ6160630  
Lot 3 CZ61605PZY

**Evaluation subject** : Small-WATT packages with Mono-component lead-frame

**Author** : D. Casiraghi

**Analysis status:**     RUNNING                       COMPLETED

### ANALYSIS PROGRAM

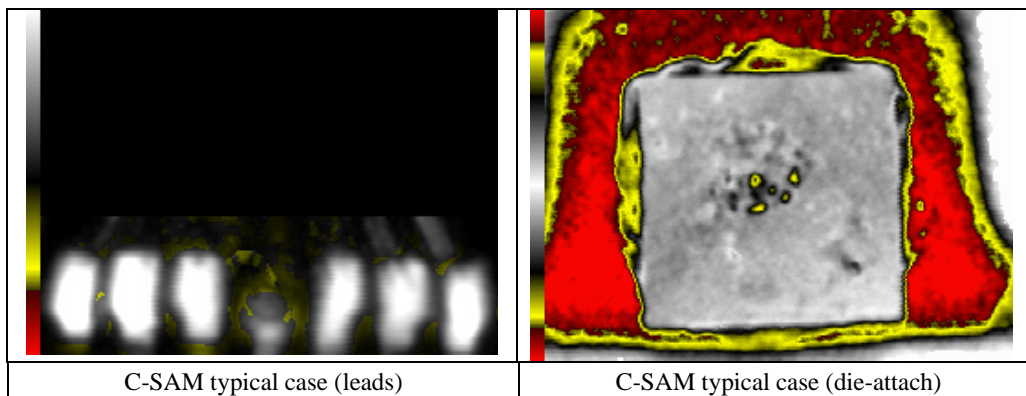
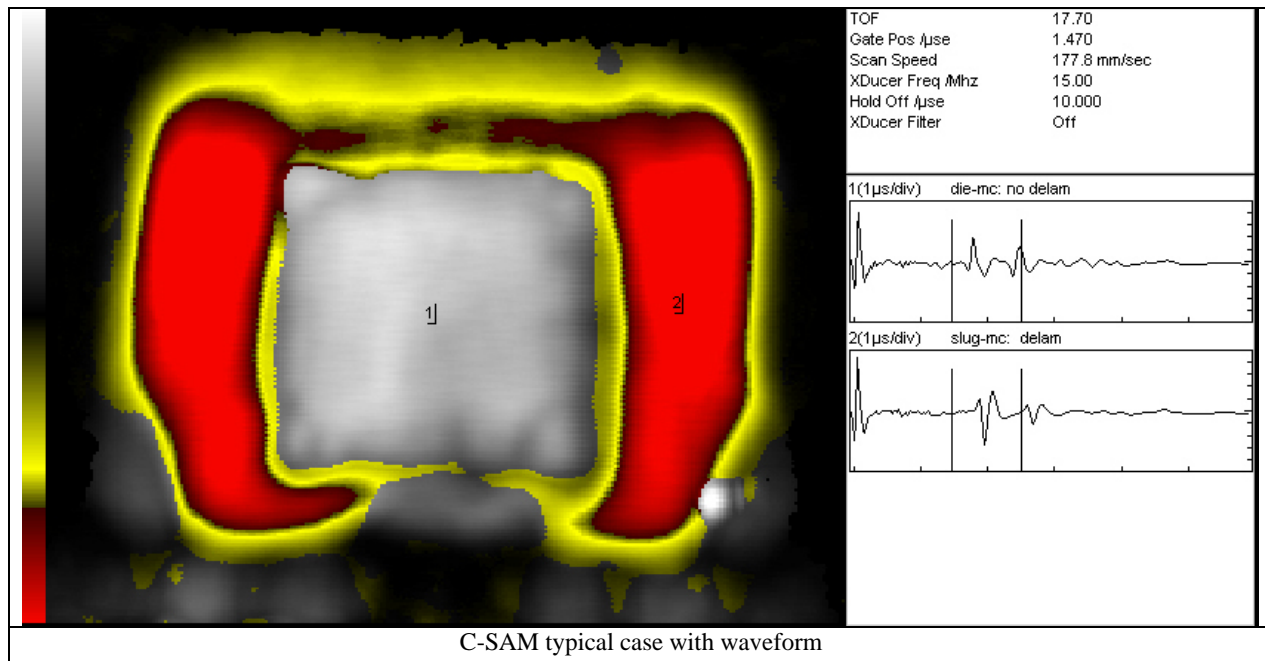
DESTRUCTIVE ITEMS				NON DESTRUCTIVE ITEMS		WHEN
Wire pull test	Ball Shear test	Internal visual	SEM inspection	SAM inspection	Other	
X		X	X	X		1000 TC
X						1000h HTS

### RESULTS SUMMARY

- SAM analysis did not show any remarkable delamination at the die-molding compound interface, on the lead tips and through the die-attach layer.
- Wire bonding strength after TC and HTS stress has been successfully verified through wire-pull test, performed in accordance with AEC-Q100 requirement. A few bonds failed in ball-lift mode, but the relevant residual pull loads are still high, especially taking into account the impact of the molding compound decap etch which is not selective to copper.
- Visual and SEM inspections after TC stress have pointed out no remarkable degradation of silicon passivation, metal interconnects, stitch bonds on internal lead-tips.

TECHNICAL CODE	PACKAGE	ANALYSIS ITEM	STRESS TEST
K87X*L570TOX	HEPTAWATT	SAM inspection	1000 TC (-65/+150°C)

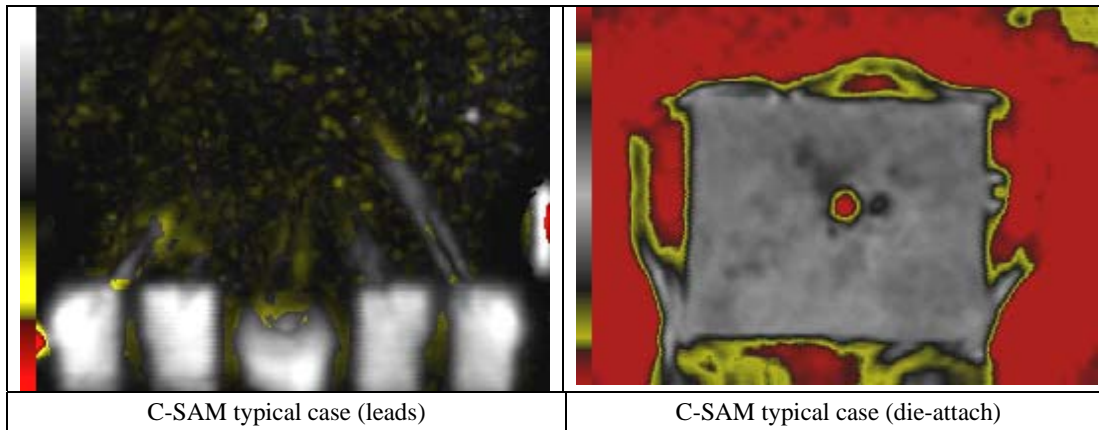
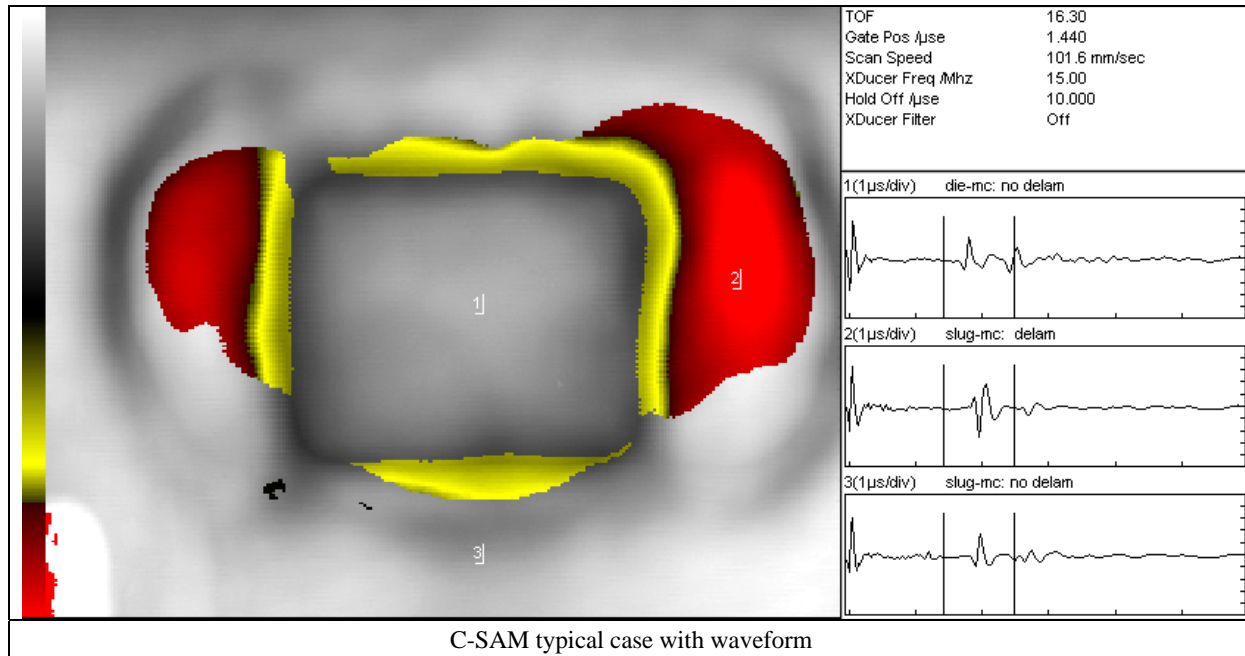
TEST EQUIPMENT: SONOSCAN D9000 (Scanning Acoustic Microscope)



Lot	Sample size	Defective parts (delamination)			
		die-mold (C-scan)	die-attach (C-scan)	l/f-mold (C-scan)	diepad-mold (C-scan)
CZ6160630-1	5	0/5	0/5	0/5	5/5
CZ6160630-2	5	0/5	0/5	0/5	5/5
Transducer frequency (MHz)		15	50	15	15

TECHNICAL CODE	PACKAGE	ANALYSIS ITEM	STRESS TEST
K87E*L540DAX	PENTAWATT	SAM inspection	1000 TC (65/+150°C)

TEST EQUIPMENT: SONOSCAN D9000 (Scanning Acoustic Microscope)



Lot	Sample size	Defective parts (delamination)			
		die-mold (C-scan)	die-attach (C-scan)	l/f-mold (C-scan)	diepad-mold (C-scan)
CZ61605PZY	5	0/5	0/5	0/5	5/5
Transducer frequency (MHz)		15	50	15	15

TECHNICAL CODE	PACKAGE	LOTS	ANALYSIS ITEM
L570TOX - L540DAX	HW - PW	CZ6160630-1, CZ6160630-2, CZ61605PZY	Internal visual

**ANALYSIS SUMMARY:**

WHAT	WHEN	SAMPLE SIZE /LOTS	RESULT
Passivation and metal	ES(100TC+168PP)	5pcs /Lot1	Minor passivation crack (photo 1-3)
Passivation and metal	ES(100TC+168PP)	5pcs /Lot2	Minor passivation crack (photo 4-6)
Passivation and metal	ES(100TC+168PP)	5pcs /Lot3	Minor passivation crack (photo 7-9)

**DOCUMENTATION:**

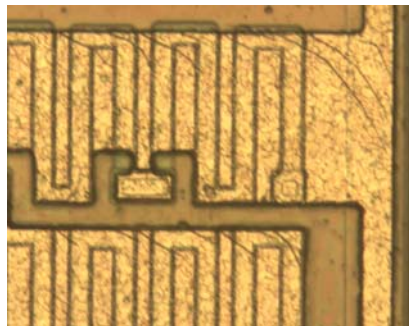


Photo 1

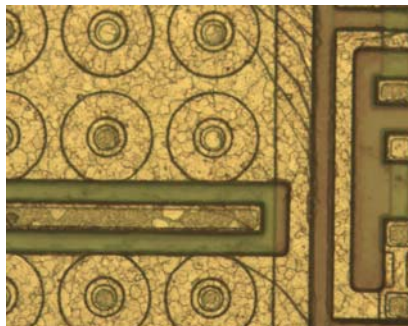


Photo 2

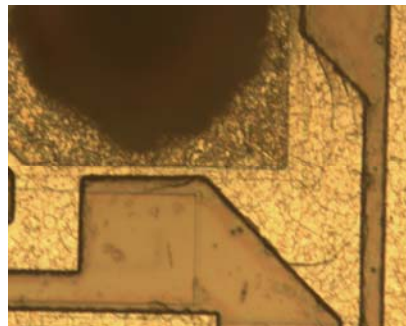


Photo 3

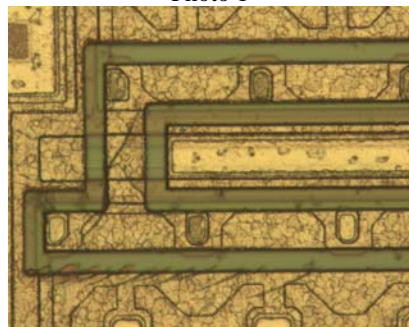


Photo 4

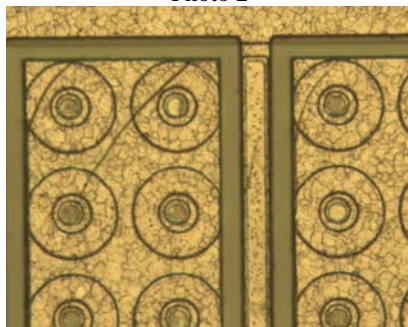


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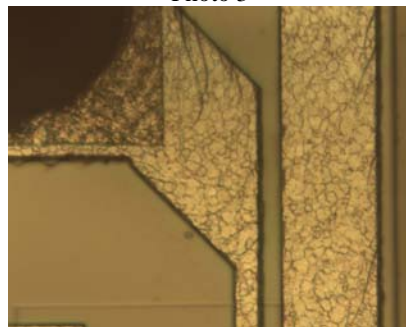


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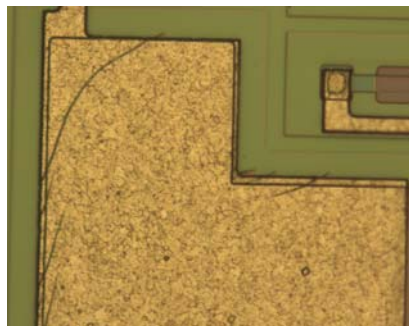


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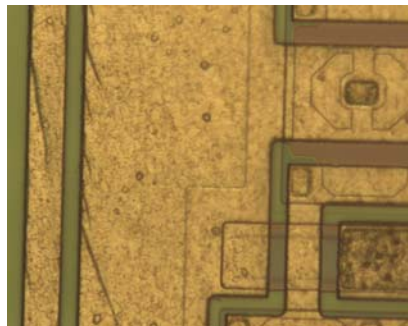


Photo 8



Photo 9

**TEST EQUIPMENT:** LEICA (Optical Microscope)



TECHNICAL CODE	PACKAGE	LOT	ANALYSIS ITEM
L570TOX - L540DAX	HW - PW	CZ6160630-1, CZ6160630-2, CZ61605PZY	SEM inspection

**ANALYSIS SUMMARY:**

WHAT	WHEN	SAMPLE SIZE	RESULT
Stitch-bond on lead	JL3+1000TC (-55/+150°C)	5pcs/lot	No visible degradation
Stitch-bond on lead	JL3+1000TC (-55/+150°C)	5pcs/lot	No visible degradation
Stitch-bond on lead	JL3+1000TC (-55/+150°C)	5pcs/lot	No visible degradation

**DOCUMENTATION:**



Photo 1

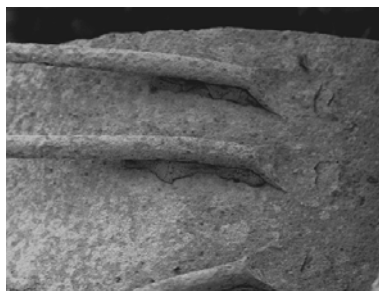


Photo 2

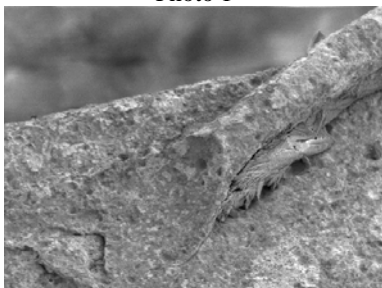
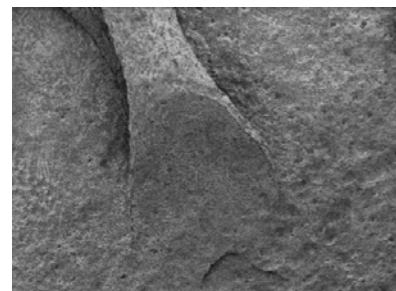
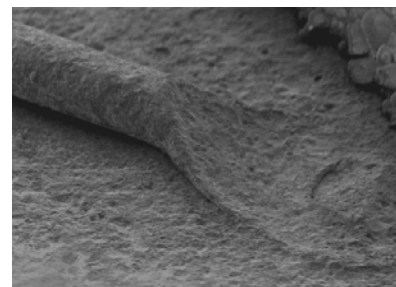
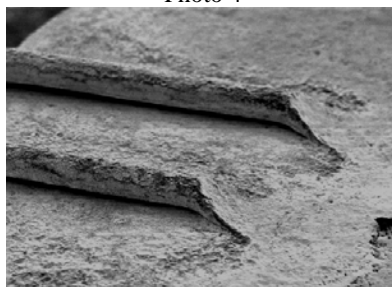
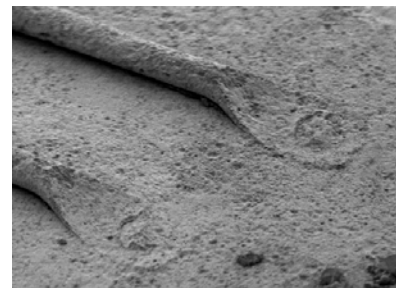


Photo 3



Photo 4

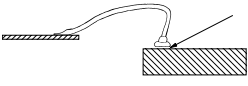
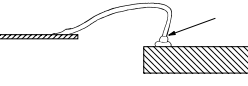
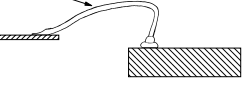
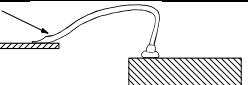


TEST EQUIPMENT: HITACHI (Scanning Electron Microscope)

TECHNICAL CODE	PACKAGE	LOT	ANALYSIS ITEM
L570TOX - L540DAX	HW - PW	CZ6160630-1, CZ6160630-2, CZ61605PZY	Wire pull-test

Wire type : Cu, 2 mil  
 LSL (g) : 10.50

Sample size (pcs) : 5  
 Sample size (wires) : 60

Failure mode	1000 TC (-65+150°C)			
		L570 lot1	L570 lot2	L540 lot3
<b>1: BALL LIFT</b> 	mean (g)	-	-	-
	stdev (g)	-	-	-
	min (g)	-	-	19.07
	max (g)	-	-	19.07
	occurrence	-	-	3%
<b>2: BALL NECK</b> 	mean (g)	34.28	30.88	30.63
	stdev (g)	2.30	5.16	2.75
	min (g)	32.65	22.92	27.10
	max (g)	35.90	36.51	35.29
	occurrence	3%	14%	30%
<b>3: LOOP CENTRE</b> 	mean (g)	30.32	30.27	35.51
	stdev (g)	6.22	4.68	6.07
	min (g)	11.68	19.13	23.95
	max (g)	44.42	44.08	47.02
	occurrence	95%	86%	64%
<b>4: BROKEN WELD</b> 	mean (g)	-	-	-
	stdev (g)	-	-	-
	min (g)	22.86	-	36.65
	max (g)	22.86	-	36.65
	occurrence	2%	-	3%

**Remarks:** neither abnormal break loads, nor forbidden failure modes. AEC-Q100 criteria after TC passed.

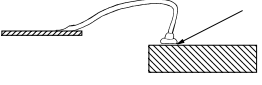
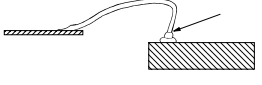
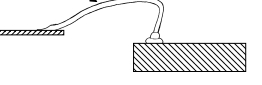
TECHNICAL CODE	PACKAGE	LOT	ANALYSIS ITEM
L570TOX - L540DAX	HW - PW	CZ6160630-1, CZ6160630-2, CZ61605PZY	Wire pull-test

Wire type : Cu, 2 mil

Sample size (pcs) : 5

LSL (g) : 10.50

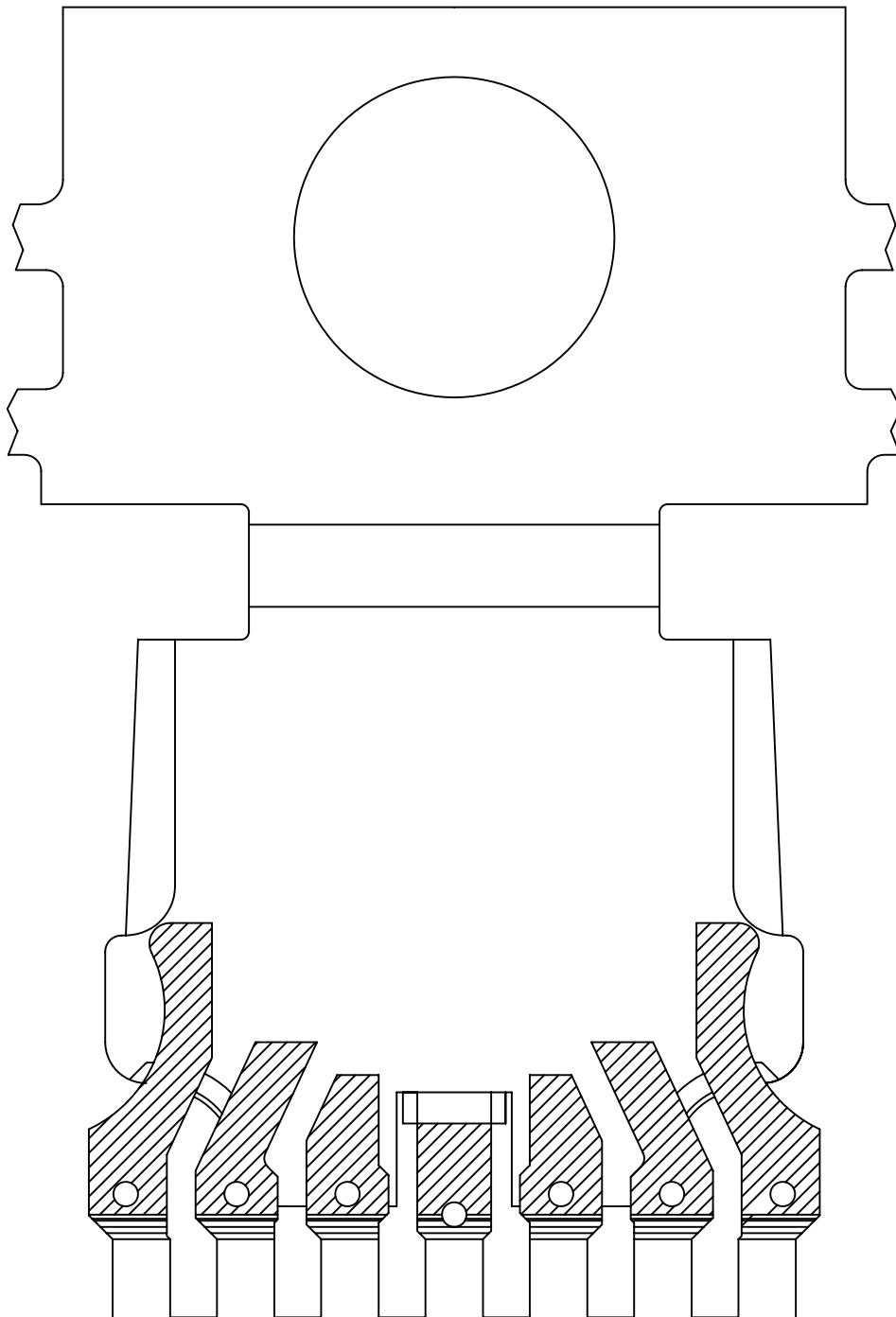
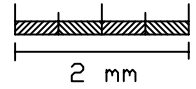
Sample size (wires) : 60

Failure mode	1000h HTS			
	L570 lot1	L570 lot2	L540 lot3	
<b>1: BALL LIFT</b>	mean (g)	-	-	19.96
	stdev (g)	-	-	0.15
	min (g)	-	-	19.85
	max (g)	-	-	20.07
	occurrence	-	-	5%
<b>2: BALL NECK</b>	mean (g)	58.54	61.49	36.36
	stdev (g)	6.81	11.80	3.10
	min (g)	53.21	49.40	34.73
	max (g)	66.22	72.97	41.01
	occurrence	8%	4%	9%
<b>3: LOOP CENTRE</b>	mean (g)	38.93	38.06	38.26
	stdev (g)	11.22	11.48	11.15
	min (g)	12.15	24.52	26.80
	max (g)	66.92	78.25	73.51
	occurrence	92%	96%	86%



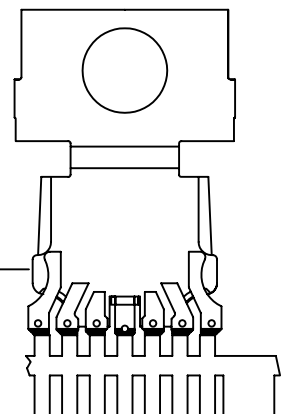
# BOND DIAGRAM FOR BICOMPONENT FRAME

PACKAGE:     P023     PAD SIZE:  $\frac{5.90 \times 4.90 \text{ mm}}{232 \times 193 \text{ mils}}$



 WELDING AREA

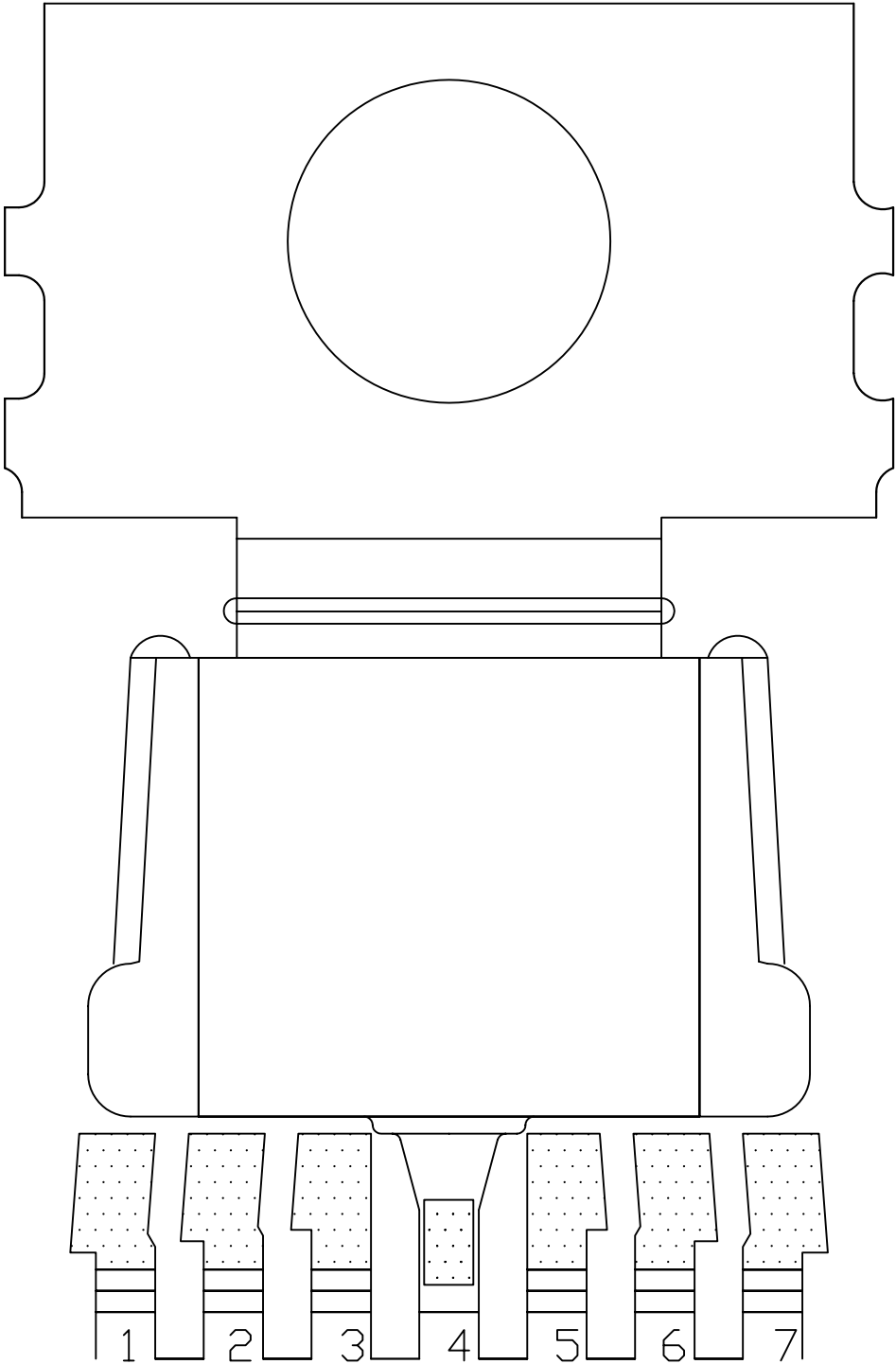
PIN N.1



HWATT 7L, BLANK BOND DIAGRAM REF. 7085438  
REMARK : E.S.D. PROGRAM IS MANDATORY

# BONDING DIAGRAM FOR MONOCOMPONENT

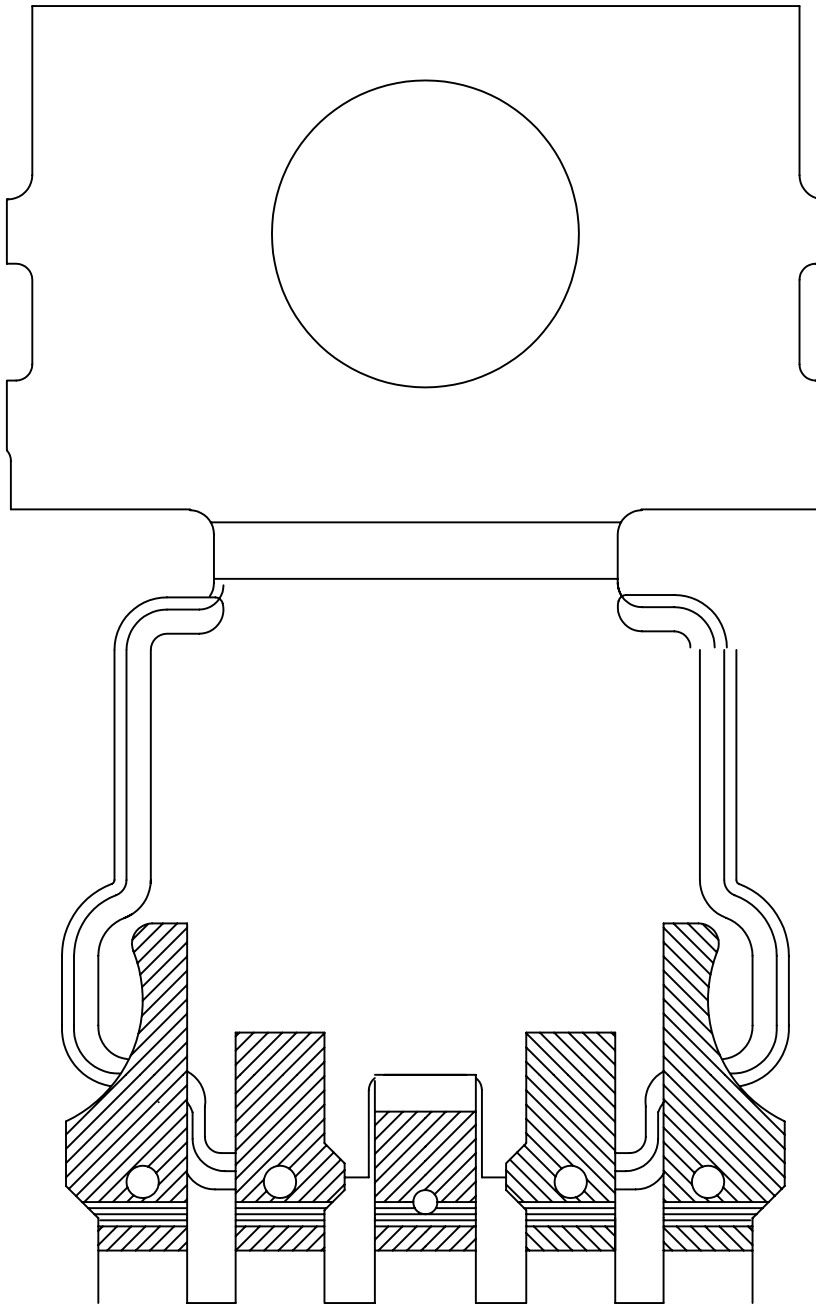
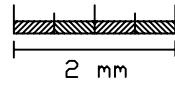
PAD SIZE:  $\frac{232 \times 212 \text{ mils}}{5.90 \times 5.40 \text{ mm}}$



HWATT 7L, BLANK BOND DIAGRAM REF.: 7X BSK  
REMARK : E.S.D. PROGRAM IS MANDATORY

# BOND DIAGRAM FOR BICOMPONENT FRAME

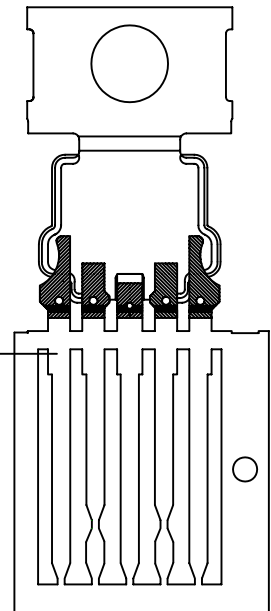
PACKAGE:     P023     PAD SIZE:  $\frac{5.90 \times 4.90 \text{ mm}}{232 \times 193 \text{ mils}}$



 WELDING AREA

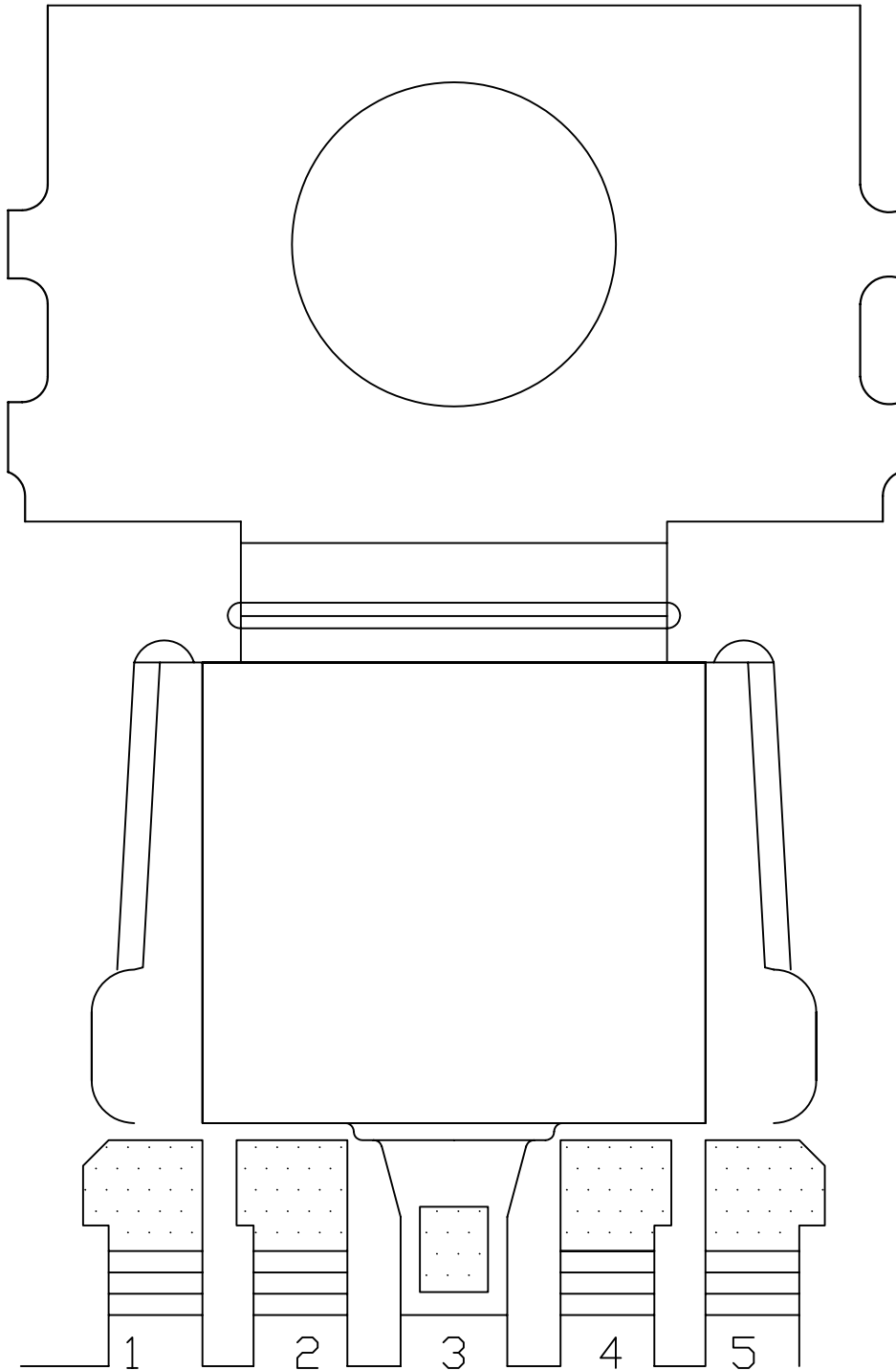
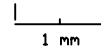
PIN N.1

PWATT 5L, BLANK BOND DIAGRAM REF. 7190575  
REMARK : E.S.D. PROGRAM IS MANDATORY



# BONDING DIAGRAM FOR MONOCOMPONENT

PAD SIZE:  $\frac{232 \times 212 \text{ mils}}{5.90 \times 5.40 \text{ mm}}$



PWATT 5L, BLANK BOND DIAGRAM REF.: 7E-7Q BSK  
REMARK : E.S.D. PROGRAM IS MANDATORY

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